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(54) **Title:** METHODS, STRUCTURES AND DEVICES FOR INCREASING MEMORY DENSITY

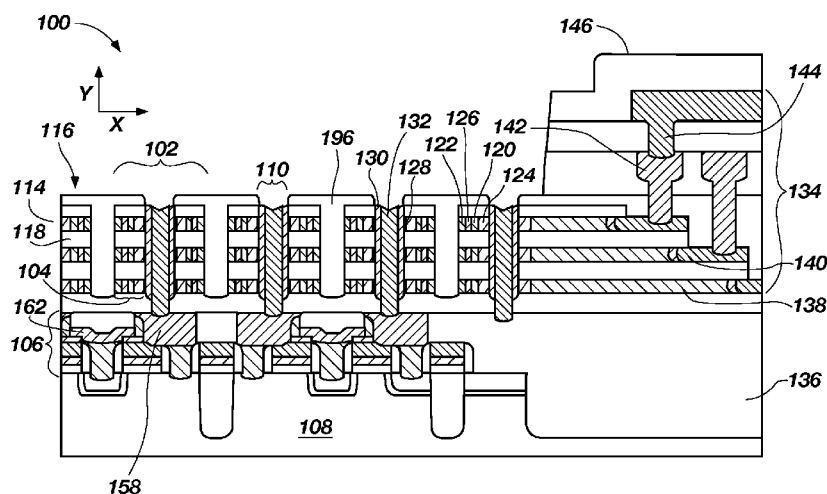


FIG. 1B

(57) **Abstract:** Non volatile memory devices comprising a memory string including a plurality of vertically superimposed diodes. Each of the diodes may be arranged at different locations along a length of the electrode and may be spaced apart from adjacent diodes by a dielectric material. The electrode may electrically couple the diodes of the memory strings to one another and to another memory device, such as, a MOSFET device. Methods of forming the non volatile memory devices as well as intermediate structures are also disclosed.